

1 MEG x 16, 2 MEG x 8 CMOS Mask Mask Programmable ROM

FEATURES

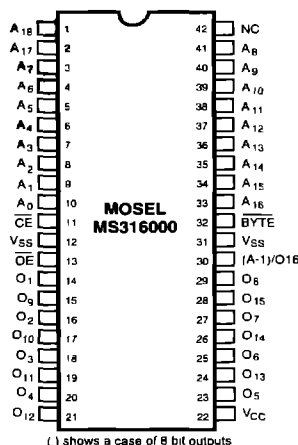
- Two organizations selectable by $\overline{\text{BYTE}}$ pin
- High Speed: 100ns (max)
Slow Speed: 200ns (max)
- Low Power:
 - Active 30mW @ 1 MHz
300mW @ 10 MHz
 - Standby 55μW (max) CMOS input level
- 3-volt operation - portable battery applications
- Short production turn-around time
- Fully static operation - no clock required
- Automatic power-down ($\overline{\text{CE}}$)
- Address transition detection to eliminate DC power
- High noise immunity
- Complete TTL compatibility
- Built-in testability with User I.D. ROM codes
- 3-state outputs for wired-OR expansion
- Standard JEDEC 42-pin DIP EPROM or 64-pin plastic QFP pinouts
- EPROMs accepted as program data input

DESCRIPTION

The MS316000 is an 16 Mb CMOS Silicon gate mask-programmable static read only memory organized as 1,048,576 words by 16 bits or 2,097,152 words by 8 bits, selectable by $\overline{\text{BYTE}}$ pin.

The MS316000 is designed to be compatible to all microprocessors and similar applications where high-speed, low power, low cost, mass storage and simple interfacing are important design considerations.

PIN CONFIGURATIONS



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BLOCK DIAGRAM

